

MRF846

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

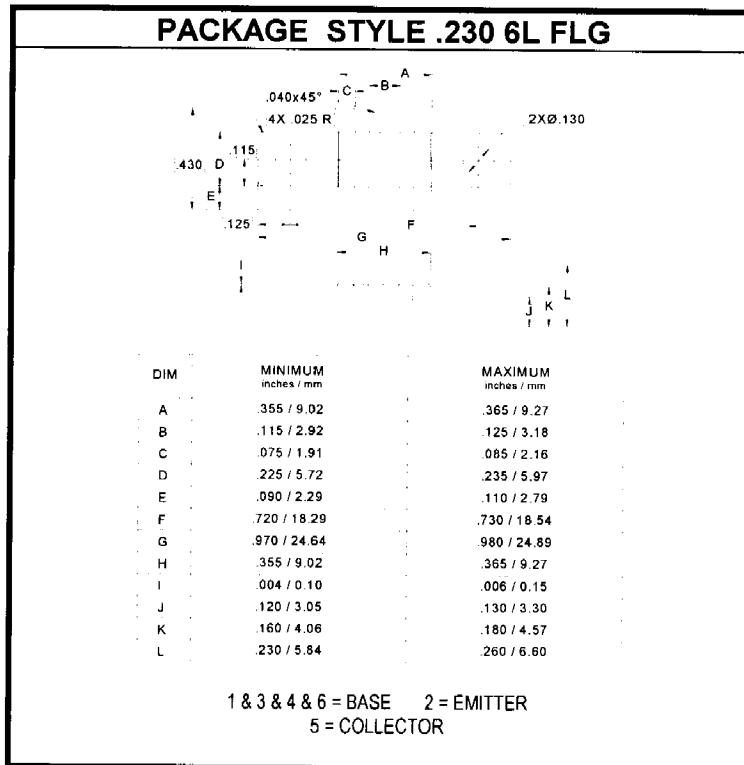
The **MRF846** is Designed for UHF Large-Signal, Common Base Amplifier Applications Up to 960 MHz.

FEATURES INCLUDE:

- Input Matching Network
- Min Gain 4.3 dB
- Gold Metalization

MAXIMUM RATINGS

I_C	14 A
V_{CBO}	36 V
V_{CEO}	16 V
P_{DISS}	150 W @ $T_C = 25^\circ C$
T_J	$-55^\circ C$ to $+200^\circ C$
T_{STG}	$-55^\circ C$ to $+150^\circ C$
θ_{JC}	1.17 $^\circ C/W$



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 50$ mA	36			V
BV_{CEO}	$I_C = 50$ mA	16			V
BV_{EBO}	$I_E = 100$ mA	4.0			V
I_{CBO}	$V_{CE} = 15$ V			10	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 2.0$ mA	10		150	---
C_{OB}	$V_{CB} = 12.5$ V $f = 1.0$ MHz		85	100	pF
P_G η_c	$V_{CE} = 12.5$ V $I_{CQ} = 50$ mA $P_{OUT} = 40$ W $f = 870$ MHz	4.3 50	5.2 55		dB %



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